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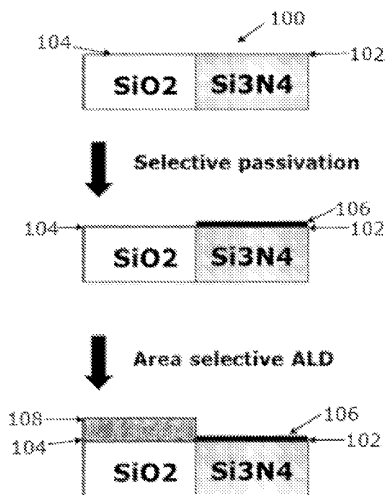
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(54) Title: AREA SELECTIVE DEPOSITION OF METAL FILM ON SILICON CONTAINING SURFACES UTILIZING HALIDES

FIG. 1



(57) Abstract: A method for selectively passivating a surface of a substrate, wherein the surface of the substrate includes at least a first surface comprising silicon nitride and at least a second surface comprising a material other than silicon nitride. The method includes the step of exposing the surface to at least one organic halide wherein the organic halide selectively reacts with the silicon nitride to passivate the first surface thereby leaving the second surface substantially unreacted.

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